

# NTST30100SG, NTSB30100S-1G

## Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.39\text{ V}$  at  $I_F = 5\text{ A}$

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

### Typical Applications

- Switching Power Supplies including Notebook/Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing Diodes
- Reverse Battery Protection
- Instrumentation

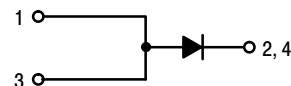
### Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

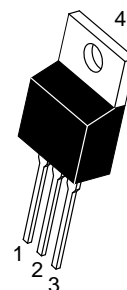


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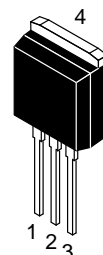
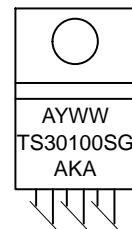
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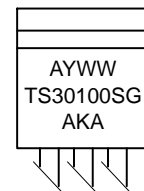
### MARKING DIAGRAMS



TO-220  
CASE 221A  
STYLE 6



i<sup>2</sup>PAK (TO-262)  
CASE 418D  
STYLE 3



A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package  
AKA = Polarity Designator

### ORDERING INFORMATION

Device	Package	Shipping†
NTST30100SG	TO-220 (Pb-Free)	50 Units/Rail
NTSB30100S-1G	TO-262 (Pb-Free)	50 Units/Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTST30100SG, NTSB30100S-1G

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	100	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 105^\circ\text{C}$ )	$I_{F(AV)}$	30	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 95^\circ\text{C}$ )	$I_{FRM}$	60	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	250	A
Operating Junction Temperature	$T_J$	-40 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 70	$^\circ\text{C}/\text{W}$

## ELECTRICAL CHARACTERISTICS

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) ( $I_F = 5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 30\text{ A}$ , $T_J = 25^\circ\text{C}$ )  ( $I_F = 5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 30\text{ A}$ , $T_J = 125^\circ\text{C}$ )	$V_F$	0.47 0.55 0.84  0.39 0.51 0.7	- - 0.95  - - 0.78	V
Maximum Instantaneous Reverse Current (Note 1) ( $V_R = 70\text{ V}$ , $T_J = 25^\circ\text{C}$ ) ( $V_R = 70\text{ V}$ , $T_J = 125^\circ\text{C}$ )  (Rated dc Voltage, $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$I_R$	27 11  70 23	   1000 45	$\mu\text{A}$ mA  $\mu\text{A}$ mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

TYPICAL CHARACTERISTICS

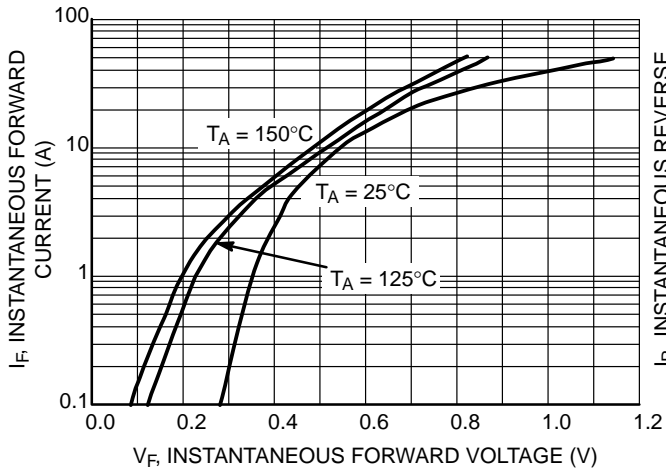


Figure 1. Typical Instantaneous Forward Characteristics

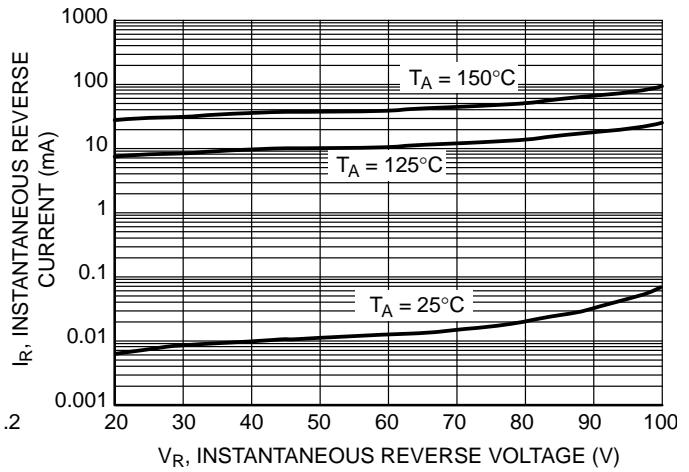


Figure 2. Typical Reverse Characteristics

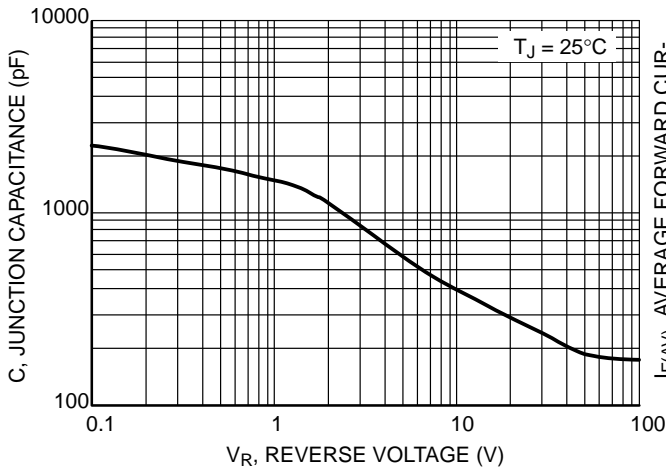


Figure 3. Typical Junction Capacitance

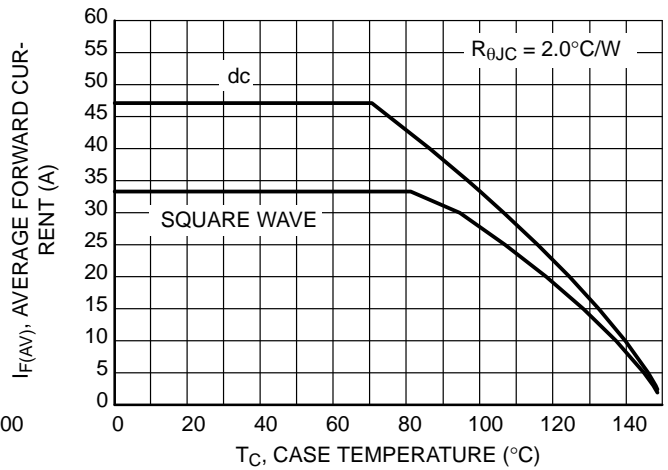


Figure 4. Current Derating, Case

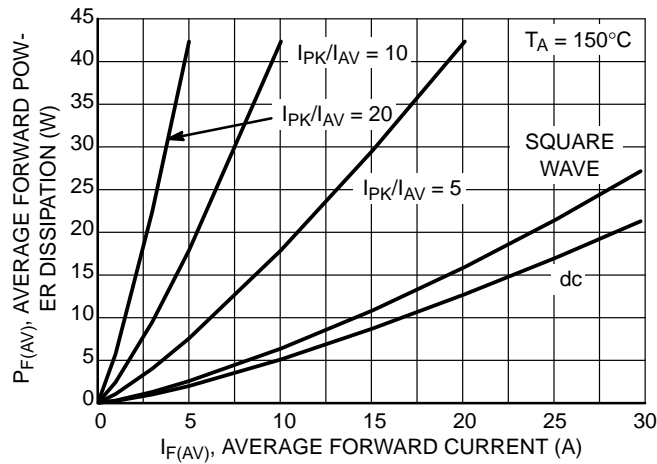


Figure 5. Forward Power Dissipation

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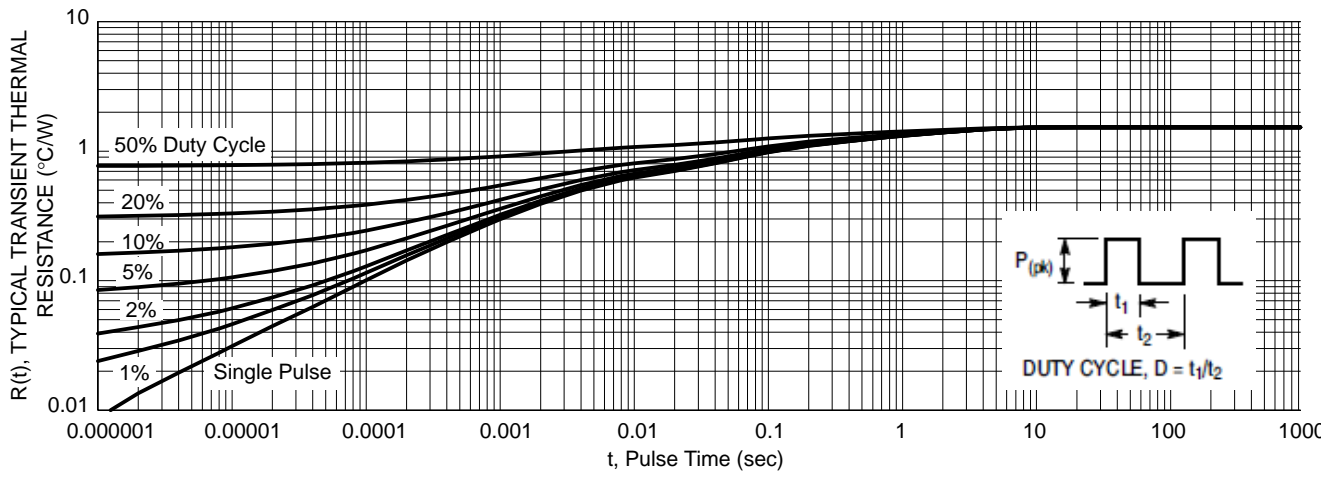
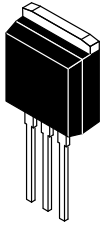


Figure 6. Typical Transient Thermal Response, Junction-to-Case

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

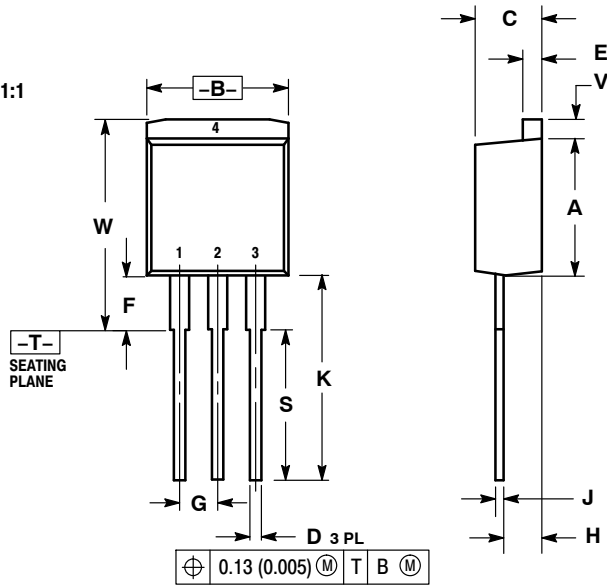
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SCALE 1:1

I<sup>2</sup>PAK (TO-262)  
CASE 418D-01  
ISSUE D

DATE 16 OCT 2007



NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.380	8.51	9.65
B	0.380	0.406	9.65	10.31
C	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
E	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
H	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 2:

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

STYLE 3:

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

STYLE 4:

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

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